Abstracts

GaAs JFET Front-End MMICs for L-Band Personal Communications

T. Ohgihara, S. Kusunoki, M. Wada and Y. Murakami. "GaAs JFET Front-End MMICs for L-Band Personal Communications." 1993 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 93.1 (1993 [MCS]): 9-12.

GaAs JFET low noise and low distortion amplifier and mixer MMICs for front-end use in L-band personal communications have been developed. These MMICs can be operated by a 3.0 V single biasing supply with a very low current dissipation of 4.0 mA. In order to achieve excellent low intermodulation distortion, a current mirror active biasing circuit using enhancement-mode JFETs, and a resistive mixing configuration were adopted.

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